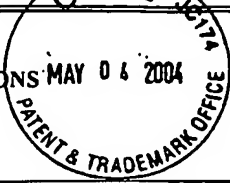


Form PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)			Atty. Docket No. 50422-7	Serial No. 10/761,275
	Applicant Steven E. Hill			
	Filing Date January 22, 2004		Group 2813	

OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

TN	AP	Giorgia Franzò, et al.; Er ³⁺ IONS-Si NANOCRYSTALS INTERACTIONS AND THEIR EFFECTS ON THE LUMINESCENCE PROPERTIES; Applied Physics Letters, Vol. 76, No. 16, 17 April 2000, pp. 2167-2169.
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	AU	A.J. Kenyon, et al.; LUMINESCENCE FROM ERBIUM-DOPED SILICON NANOCRYSTALS IN SILICA: EXCITATION MECHANISMS; Journal of Applied Physics, Vol. 91, No. 1, 1 January 2002, pp. 367-374.
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	aa	P.S. Andry, et al.; GROWTH OF Er-DOPED SILICON USING METALORGANICS BY PLASMA-ENHANCED CHEMICAL VAPOR DEPOSITION; J. Appl. Phys. 80 (1), 1 July 1996, pp. 551-558.
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EXAMINER	T. NGUYEN	DATE CONSIDERED	10/28/05
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EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		Applicant STEVEN E. HILL	
		Filing Date January 22, 2004	Group 2813

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPROPRIATE
TN ↓	AA	5,667,905	1997.09.16	Campanisano, Salvatore Ugo et al.	—	—	
	AB	6,255,669	2001.07.03	Birkhahn, Ronald H. et al.	—	—	
	AC	US 2003/034486	2003.02.20	Korgel, Brian A.	—	—	
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
TN ↓	AH	101 04 193	2002.08.01	DE	—	—		
	AI	2001 203382	2001.07.11	JP	—	—		
	AJ	1 134 799	2001.09.19	EP	—	—		
	AK	WO 02/061815	2002.08.08	DE	—	—		
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TN ↓	AM	Orlov, L.K. et al.	COMPARITIVE ANALYSIS OF LIGHT EMMITTING PROPERTIES OF Si:Er AND Ge/Si _{1-x} Ge _x EPITAXIAL STRUCTURES OBTAINED BY MBE METHOD. <i>Gettering and Defect Engineering in Semiconductor Technology, Solid State Phenomena (FORMERLY Part B of "Diffusion and Defect Data [0377-6883])</i> . Vol 69 until 70, 1999. Pages 377-382. ISSN:1012-0394.
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	AO	Yun, F. et al.	ROOM TEMPERATURE SINGLE-ELECTRON NARROW-CHANNEL MEMORY WITH SILICON NANODOTS EMBEDDED IN SiO ₂ MATRIX. <i>Japanese Journal of Applied Physics</i> . Publication Office Japanese Journal of Applied Physics. Vol. 39, no. 8A Part II. August 1, 2000. Tokyo, Japan. Pages L792- L795.
EXAMINER T. NGUYEN			DATE CONSIDERED 10/28/05

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